

Nam Han

List of Publications by Year in descending order

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31
papers

375
citations

759233

12
h-index

839539

18
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31
all docs

31
docs citations

31
times ranked

679
citing authors

#	ARTICLE	IF	CITATIONS
1	Wafer-scale and selective-area growth of high-quality hexagonal boron nitride on Ni(111) by metal-organic chemical vapor deposition. <i>Scientific Reports</i> , 2019, 9, 5736.	3.3	42
2	Comparison of various surface textured layer in InGaN LEDs for high light extraction efficiency. <i>Optics Express</i> , 2011, 19, 3637.	3.4	39
3	Chemically modified multilayer graphene with metal interlayer as an efficient current spreading electrode for InGaN/GaN blue light-emitting diodes. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 145101.	2.8	35
4	Impact of two-floor air prism arrays as an embedded reflector for enhancing the output power of InGaN/GaN light emitting diodes. <i>Applied Physics Letters</i> , 2009, 95, 221110.	3.3	21
5	Pressure-Dependent Growth of Wafer-Scale Few-layer h-BN by Metal-Organic Chemical Vapor Deposition. <i>Crystal Growth and Design</i> , 2017, 17, 2569-2575.	3.0	21
6	Role of hydrogen carrier gas on the growth of few layer hexagonal boron nitrides by metal-organic chemical vapor deposition. <i>AIP Advances</i> , 2017, 7, .	1.3	20
7	Improvement of Light Output Power in InGaN/GaN Light-Emitting Diodes with a Nanotextured GaN Surface Using Indium Tin Oxide Nanospheres. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 102104.	1.5	16
8	Fabrication and Characteristics of GaN-Based Light-Emitting Diodes with a Reduced Graphene Oxide Current-Spreading Layer. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 22451-22456.	8.0	15
9	Enhanced thermal stability of reduced graphene oxide-Silicon Schottky heterojunction solar cells via nitrogen doping. <i>Materials Science in Semiconductor Processing</i> , 2017, 59, 45-49.	4.0	15
10	Effect of embedded silica nanospheres on improving the performance of InGaN/GaN light-emitting diodes. <i>Optics Express</i> , 2011, 19, 2029.	3.4	14
11	Stimulated N-doping of reduced graphene oxide on GaN under excimer laser reduction process. <i>Materials Letters</i> , 2014, 116, 412-415.	2.6	13
12	High performance of InGaN light-emitting diodes by air-gap/GaN distributed Bragg reflectors. <i>Optics Express</i> , 2012, 20, 9999.	3.4	12
13	Enhanced light emission in blue light-emitting diodes by multiple Mie scattering from embedded silica nanosphere stacking layers. <i>Optics Express</i> , 2011, 19, 23429.	3.4	11
14	Enhancement of light output power in GaN-based light-emitting diodes using indium tin oxide films with nanoporous structures. <i>Thin Solid Films</i> , 2011, 520, 437-441.	1.8	11
15	Defect-Mediated In-Plane Electrical Conduction in Few-Layer sp ² -Hybridized Boron Nitrides. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 17287-17294.	8.0	10
16	Self-Assembled Periodic Silica Nanosphere Arrays on Wet-Etched Patterned Sapphire Substrate for a High-Light-Extraction-Efficiency Light-Emitting Diode. <i>IEEE Electron Device Letters</i> , 2011, 32, 527-529.	3.9	9
17	Reduced junction temperature and enhanced performance of high power light-emitting diodes using reduced graphene oxide pattern. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 265102.	2.8	9
18	Synthesis and optical properties of sword-like GaN nanorods clusters. <i>Current Applied Physics</i> , 2009, 9, S114-S117.	2.4	8

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19	Selective Defect Blocking by Self-Assembled Silica Nanospheres for High Quality GaN Template. <i>Electrochemical and Solid-State Letters</i> , 2010, 13, H287.	2.2	8
20	Reduced thermal resistance of heat sink using graphene oxide decorated with copper nanoparticles. <i>Materials Research Bulletin</i> , 2019, 110, 76-81.	5.2	7
21	InGaN/GaN Light-Emitting Diode on Concave-Hexagonal-Patterned Sapphire Substrate. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 110201.	1.5	6
22	Characteristics of aluminum nitride films on hexagonal boron nitride buffer layers using various growth methods through metal organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2019, 507, 316-320.	1.5	6
23	Enhanced light output power of GaN-based light emitting diodes with overcut sideholes formed by wet etching. <i>Solid-State Electronics</i> , 2010, 54, 575-578.	1.4	5
24	Threading dislocation reduction in epitaxial GaN using V-groove patterned sapphire substrate with embedded silica nanospheres. <i>Materials Letters</i> , 2014, 123, 97-100.	2.6	5
25	Long-term stability of Si-organic hybrid solar cells with a thermally tunable graphene oxide platform. <i>RSC Advances</i> , 2016, 6, 72342-72350.	3.6	5
26	Optical and Facet-Dependent Carrier Recombination Properties of Hendecafacet InGaN/GaN Microsized Light Emitters. <i>Crystal Growth and Design</i> , 2017, 17, 3649-3655.	3.0	5
27	InGaN/GaN Light-Emitting Diodes with Overcut-Shaped Periodic Microstructures Formed by Wet Etching Process. <i>Electrochemical and Solid-State Letters</i> , 2009, 12, H299.	2.2	3
28	Air-ring microstructure arrays for enhanced light extraction from a face-up light-emitting diode. <i>Optics Letters</i> , 2013, 38, 1491.	3.3	2
29	Formation and optimization of undercut-microholes in InGaN light emitting diodes by using wet chemical etching. <i>Thin Solid Films</i> , 2012, 520, 4373-4377.	1.8	1
30	Two-step lateral growth of GaN for improved emission from blue light-emitting diodes. <i>Journal of Crystal Growth</i> , 2013, 372, 157-162.	1.5	1
31	The enhancement of the deflection effect in InGaN/GaN light-emitting diodes with an ellipsoidal air tunnel. <i>Solid-State Electronics</i> , 2012, 69, 14-17.	1.4	0